

1 ABSTRACT OF THE DISCLOSURE

2 Semiconductor processing methods include forming a plurality of
3 patterned device outlines over a semiconductor substrate, forming
4 electrically insulative partitions or spacers on at least a portion of the
5 patterned device outlines, and forming a plurality of substantially
6 identically shaped devices relative to the patterned device outlines.
7 Individual formed devices are spaced from at least one other of the
8 devices by a distance no more than a width of one of the electrically
9 insulative spacers. In such manner, device pitch is reduced by almost
10 fifty percent. According to one aspect, elongated electrically conductive
11 lines are formed. According to another aspect, capacitors are formed
12 which, according to a preferred embodiment form part of a dynamic
13 random access memory (DRAM) array.
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